

**CERTIFICATE OF TRANSMISSION BY FACSIMILE (37 CFR 1.8)**

Applicant(s): KAMALESH K. SRIVASTAVA ET AL.

Docket No.

FIS920030359US1

Application No.

10/708,649

Filing Date

05/17/2004

Examiner

THERESA T. DOAN

Group Art Unit

2814

Invention: METHOD FOR FORMING ROBUST SOLDER INTERCONNECT STRUCTURES BY REDUCING EFFECTS OF SEED LAYER

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Response to Restriction Requirement

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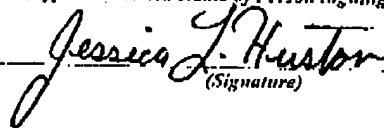
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APPLICANT: KAMALESH K. SRIVASTAVA ET AL. ) Group Art Unit: 2814  
SERIAL NUMBER: 10/708,649 )  
FILED: May 17, 2004 ) Examiner:  
FOR: METHOD FOR FORMING ROBUST ) Theresa T. Doan  
SOLDER INTERCONNECT )  
STRUCTURES BY REDUCING EFFECTS ) Confirmation No. 2648  
OF SEED LAYER )

Commissioner For Patents  
P.O. Box 1450  
Alexandria, VA. 22313-1450

**RESPONSE TO RESTRICTION REQUIREMENT**

In response to the restriction requirement mailed on May 2, 2005, and in accordance with the provisions under 37 CFR § 1.115 and 1.143, the Applicants submit the following election for further prosecution on the merits:

Election:

Applicants hereby elect, without traverse, Group II, claims 6-20, a method for forming an interconnect structure comprising annealing the semiconductor device as to cause atoms from the barrier layer to diffuse into the seed layer there underneath, wherein the annealing causes diffused regions of the seed layer to have an altered electrical resistivity and electrode potential with respect to undiffused regions of the seed layer.